



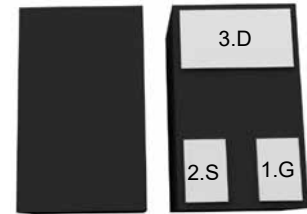
# PJM01P20KDC

## P-Channel Enhancement Mode Power MOSFET

### Features

- Low gate charge and  $R_{DS(ON)}$
- ESD protected(HBM) up to 2KV
- $V_{DS} = -20V, I_D = -0.65A$   
 $R_{DS(on)} < 850m\Omega @ V_{GS} = -4.5V$

DFN1x0.6-3L



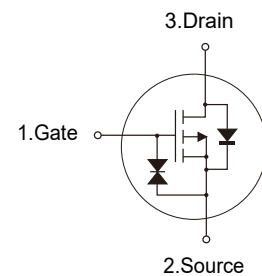
1. Gate 2.Source 3.Drain

### Applications

- Load switch and in PWM applications
- Power management

Marking Code: JP

### Schematic Diagram



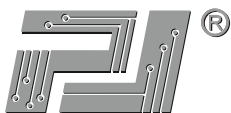
### Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	20	V
Gate-Source Voltage	$-V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$-I_D$	0.65	A
Drain Current-Pulsed <sup>Note1</sup>	$-I_{DM}$	2	A
Maximum Power Dissipation	$P_D$	0.35	W
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{STG}$	-55 to +150	°C

### Thermal Characteristics

Thermal Resistance, Junction-to-Ambient <sup>Note2</sup>	$R_{\theta JA}$	357	°C/W
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### Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$-V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	20	--	--	V
Zero Gate Voltage Drain Current	$-I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$	--	--	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 10V, V_{DS}=0V$	--	--	$\pm 10$	$\mu A$
Gate Threshold Voltage <sup>Note3</sup>	$-V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	0.35	0.62	1.2	V
Drain-Source On-Resistance <sup>Note3</sup>	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-0.5A$	--	580	850	m $\Omega$
		$V_{GS}=-2.5V, I_D=-0.3A$	--	855	1200	m $\Omega$
Forward Transconductance <sup>Note3</sup>	$g_{FS}$	$V_{DS}=-5V, I_D=-0.3A$	--	2	--	S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0V, f=1MHz$	--	71	--	pF
Output Capacitance	$C_{oss}$		--	20	--	pF
Reverse Transfer Capacitance	$C_{rss}$		--	15	--	pF
<b>Switching Characteristics</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=2.5\Omega,$ $V_{GS}=-4.5V, R_{GEN}=3\Omega$	--	4	--	nS
Turn-on Rise Time	$t_r$		--	19	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	16	--	nS
Turn-off Fall Time	$t_f$		--	25	--	nS
Total Gate Charge	$Q_g$	$V_{DS}=-10V, I_D=-0.5A,$ $V_{GS}=-4.5V$	--	1.24	--	nC
Gate-Source Charge	$Q_{gs}$		--	0.37	--	nC
Gate-Drain Charge	$Q_{gd}$		--	0.27	--	nC
<b>Source-Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>Note3</sup>	$-V_{SD}$	$V_{GS}=0V, I_S=-0.65A$	--	--	1.2	V
Diode Forward Current <sup>Note2</sup>	$-I_S$		--	--	0.65	A

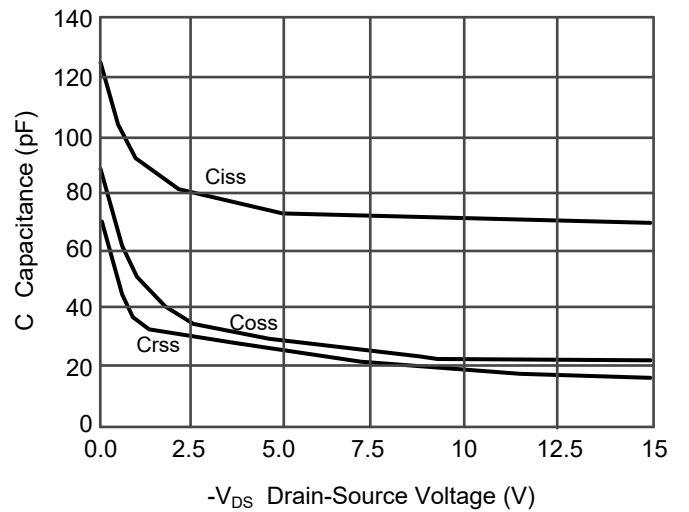
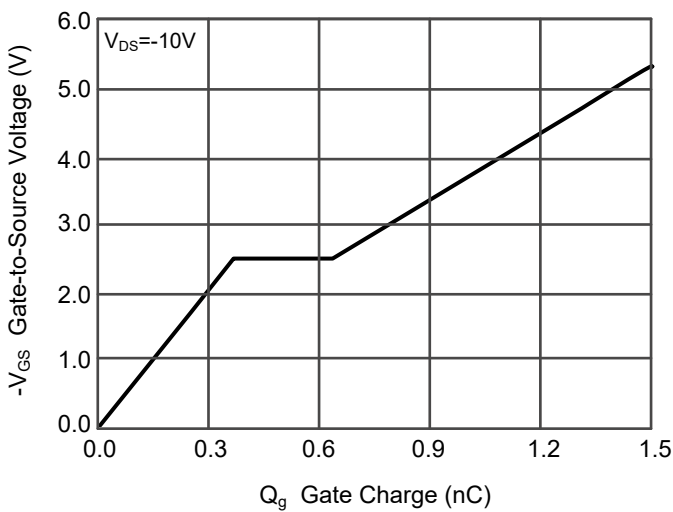
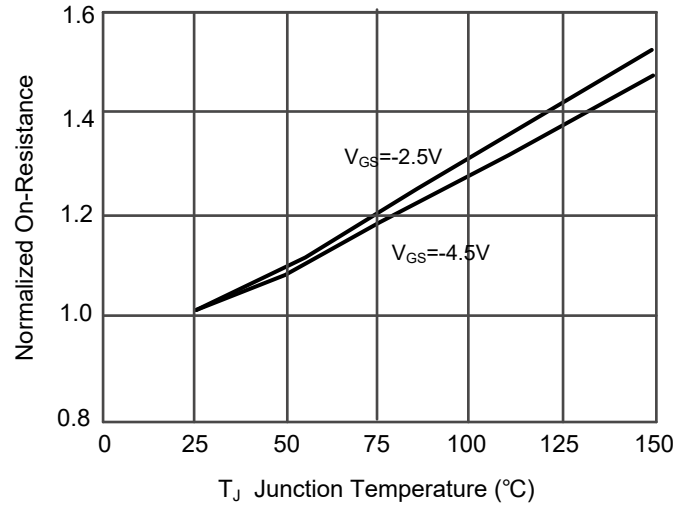
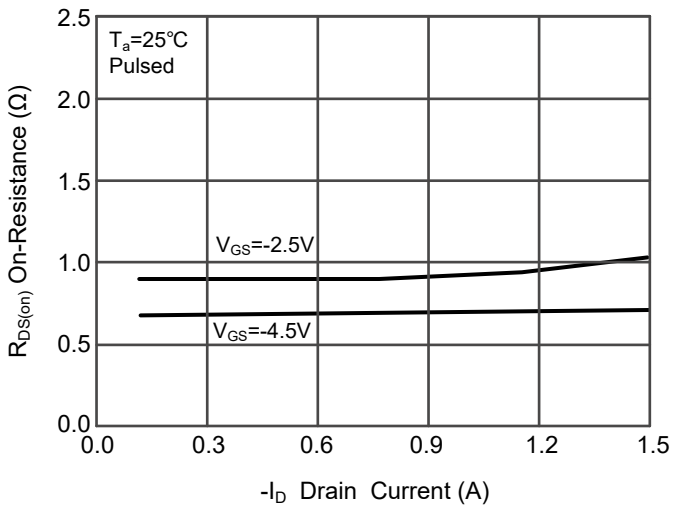
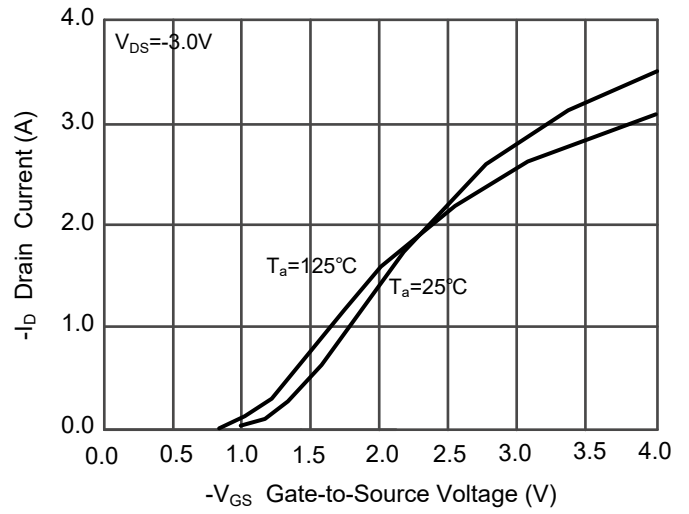
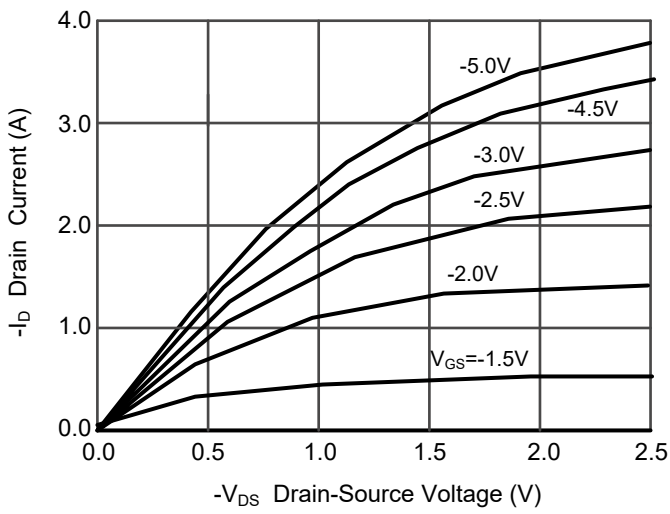
- Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.  
2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.  
3. Pulse Test: Pulse width $\leq 300\mu s$ , duty cycle $\leq 2\%$ .



# PJM01P20KDC

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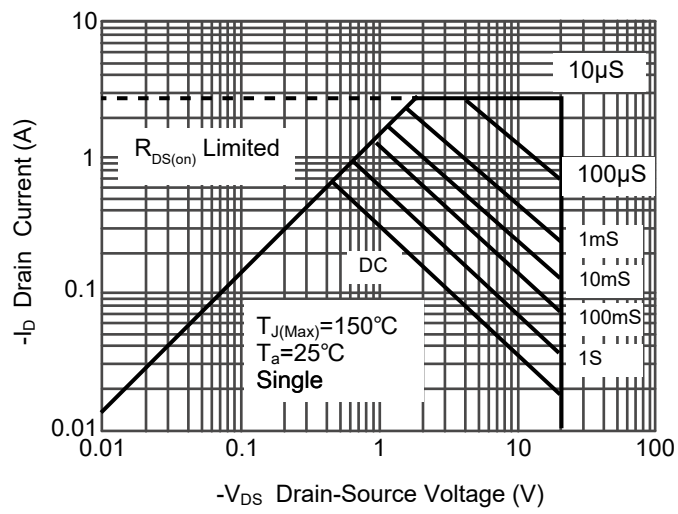
### Typical Characteristic Curves





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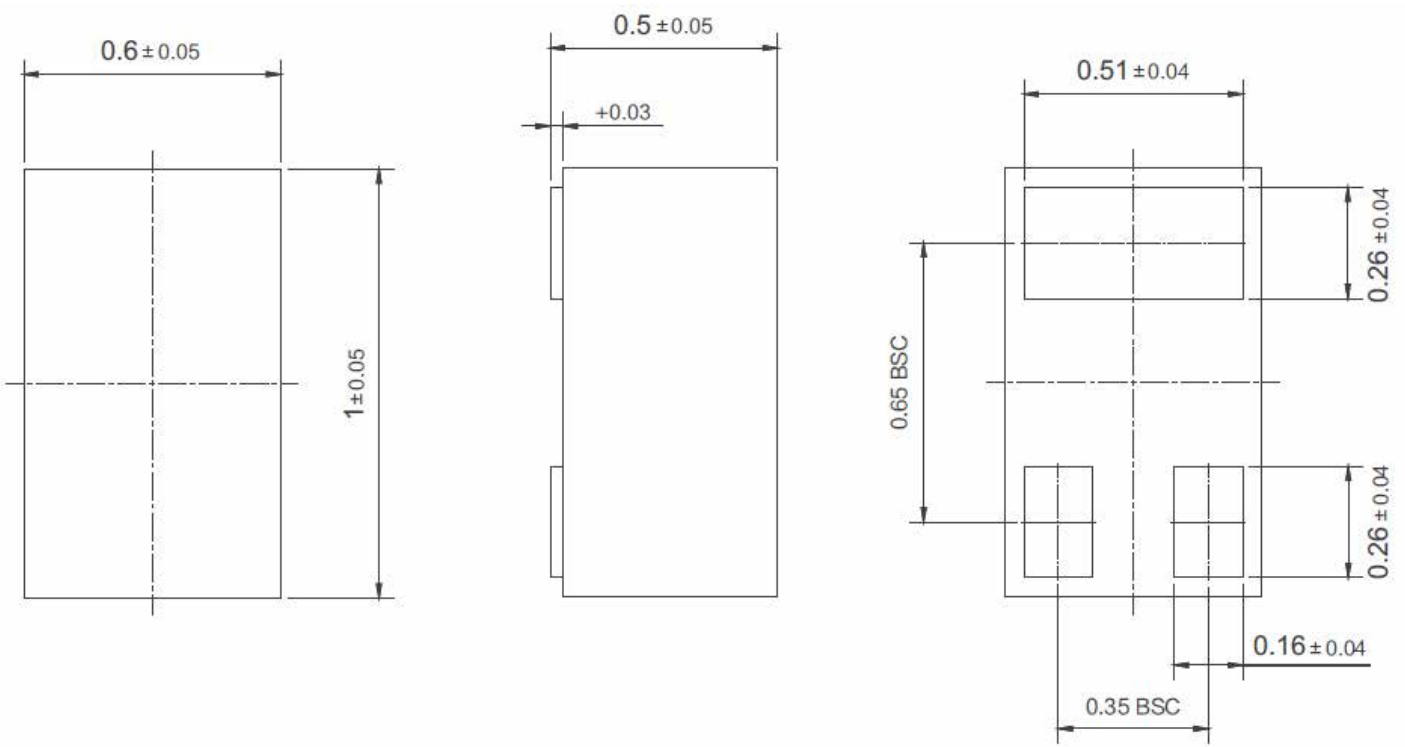
# PJM01P20KDC

## P-Channel Enhancement Mode Power MOSFET

### Package Outline

DFN1x0.6-3L-0009

Dimensions in mm



### Ordering Information

Device	Package	Shipping
PJM01P20KDC	DFN1x0.6-3L	10,000PCS/Reel&7inches